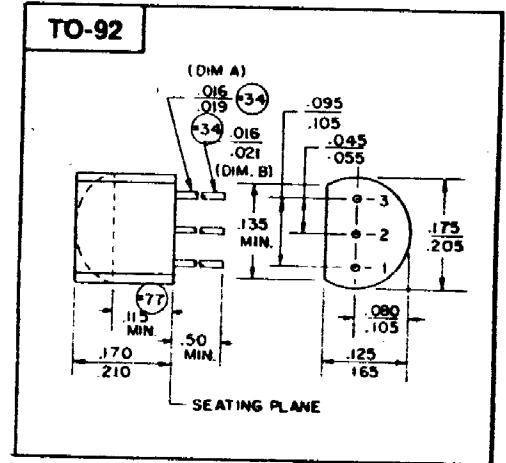


2N5249

NPN SILICON TRANSISTOR

absolute maximum ratings: (25°C) (unless otherwise specified)

Voltages			
Collector to Emitter	V_{CE0}	50	V
Emitter to Base	V_{EB0}	5	V
Collector to Base	V_{CB0}	70	V
Current			
Collector (Steady State)*	I_C	100	mA
Dissipation			
Total Power (Free Air at 25°C)†	P_T	360	mW
Total Power (Free Air at 55°C)†	P_T	260	mW
Temperature			
Storage	T_{stg}	-55 to +150	°C
Operating	T_j	+125	°C
Lead Soldering, 1/16" ± 1/32" from case for 10 seconds maximum	T_s	+260	°C



*Determined from power limitations due to saturation voltages at this current.
†Derate 3.3 mW/°C increase in ambient temperature above 25°C.

electrical characteristics: (25°C) (unless otherwise specified)

Static Characteristics

	Min.	Typ.	Max.	
Collector Cutoff Current ($V_{CB} = 50V$)			30	nA
($V_{CB} = 50V, T_A = 100°C$)			10	μA
Collector Cutoff Current ($V_{CB} = 50V$)			30	nA
Emitter Cutoff Current ($V_{EB} = 5V$)			50	nA
Forward Current Transfer Ratio ($V_{CB} = 5V, I_C = 2 mA$)	400		800	
($V_{CB} = 5V, I_C = 100 μA$)		300‡		
Collector Emitter Breakdown Voltage ($I_C = 10 mA$)	50			Volts
Collector Base Breakdown Voltage ($I_C = 10 μA$)	70			Volts
Emitter Base Breakdown Voltage ($I_E = 10 μA$)	5			Volts
Collector Saturation Voltage ($I_C = 10 mA, I_B = 1 mA$)			.125	Volts
Base Saturation Voltage ($I_C = 10 mA, I_B = 1 mA$)			.78	Volts
Base Emitter Voltage ($V_{CB} = 10V, I_C = 2 mA$)	0.5		0.9	Volts

Dynamic Characteristics

Forward Current Transfer Ratio ($V_{CB} = 5V, I_C = 2 mA, f = 1 kHz$)	h_{fe}	400	1200	
Output Capacitance, Common Base ($V_{CB} = 10V, I_B = 0, f = 1 MHz$)	C_{cb}		4.0	pF

‡Typically, a minimum of 95% of the distribution is above this value.

¶Pulse conditions: 300 μsec. duration, 2% duty cycle.

